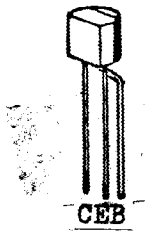
2N5447 THROUGH 2N5450

COMPLEMENTARY SILICON GENERAL PURPOSE AF TRANSISTORS

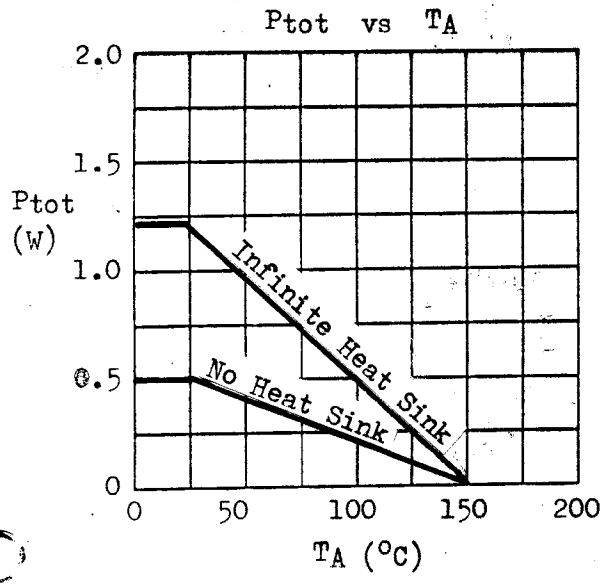
THE 2N5447, 2N5448, 2N5449, 2N5450 ARE SILICON PLANAR EPITAXIAL TRANSISTORS FOR GENERAL PURPOSE MEDIUM POWER AMPLIFIER APPLICATIONS. THE 2N5447, 2N5448 ARE PNP AND ARE COMPLEMENTARY TO THE NPN 2N5449, 2N5450 RESPECTIVELY.

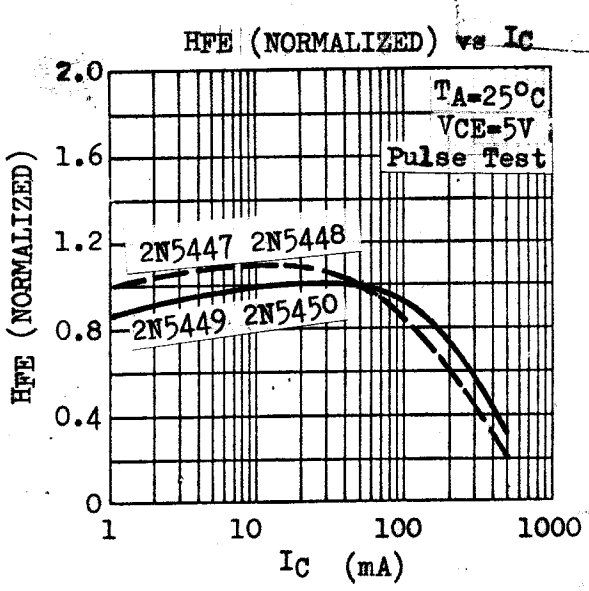
CASE TO-92F



ABSOLUTE MAXIMUM RATINGS (For p-n-p devices, voltage and current values are negative.)		2N5447(PNP)	2N5448(PNP)	2N5449(NPN) 2N5450(NPN)
Collector-Base Voltage	V_{CBO}	40V	50V	50V
Collector-Emitter Voltage	V_{CEO}	25V	30V	30V
Emitter-Base Voltage	V_{EBO}	5V	5V	5V
Collector Current	I_C	0.2A	0.2A	0.8A
Collector Peak Current ($t \leq 10mS$)	I_{CM}	0.6A	0.6A	
Total Power Dissipation ($T_C \leq 25°C$)	P_{tot}		1.2W	
($T_A \leq 25°C$)			500mW **	
Operating Junction & Storage Temperature	T_j, T_{stg}		-55 to 150°C	

** 360mW in JEDEC registration.





MICRO ELECTRONICS LTD. 38 HUNG TO ROAD, KWUN TONG, HONG KONG. TELEX 43510
KWUN TONG P. O. BOX69477 CABLE ADDRESS "MICROTRON"
TELEPHONE:- 3-430181-6 ~~3-893363, 3-892423~~
FAX: 3-410321

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	BV_{CBO}					I_C=0.1mA I_E=0
2N5447		40			V	
2N5448, 2N5449, 2N5450		50			V	
Collector-Emitter Breakdown Voltage	LV_{CEO} *					I_C=10mA I_B=0
2N5447		25			V	
2N5448, 2N5449, 2N5450		30			V	
Emitter-Base Breakdown Voltage	BV_{EBO}	5			V	I_E=0.1mA I_C=0
Collector Cutoff Current	I_{CBO}			100	nA	V_{CB}=20V I_E=0
Emitter Cutoff Current	I_{EBO}			100	nA	V_{EB}=3V I_C=0
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$*					
2N5447, 2N5448				0.25	V	I_C=50mA I_B=5mA
2N5449				0.6	V	I_C=100mA I_B=5mA
2N5450				0.8	V	I_C=100mA I_B=5mA
Base-Emitter Voltage	V_{BE} *					
2N5447, 2N5448		0.6		1.0	V	I_C=50mA V_{CE}=5V
2N5449, 2N5450		0.5		1.0	V	IC=100mA V_{CE}=2V
D.C. Current Gain 2N5447	H_{FE} *	60		300		I_C=50mA V_{CE}=5V
2N5448		30		150		I_C=50mA V_{CE}=5V
2N5449		100		300		I_C=50mA V_{CE}=2V
2N5450		50		150		I_C=50mA V_{CE}=2V
Current Gain-Bandwidth Product	f_T					
2N5447, 2N5448		100			MHz	I_C=50mA V_{CE}=5V
2N5449, 2N5450		100			MHz	IC=50mA V_{CE}=2V
Collector-Base Capacitance	Cob			12	pF	V_{CB}=10V I_E=0 f=1MHz

* Pulse Test : Pulse Width=0.3mS, Duty Cycle=1%

